

Features

- Trench Power MV MOSFET technology
- High Speed switching
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

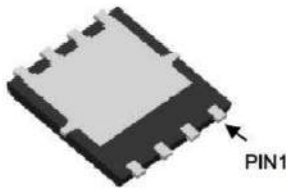
Application

- PWM application
- Load switch

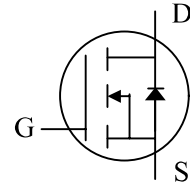
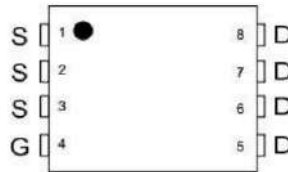


Product Summary

V_{DS}	20	V
$R_{DS(on),Typ} @ V_{GS}=4.5V$	8.7	mΩ
I_D	16	A



PDFN3.3x3.3-8



■ Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	20	V
Gate-source Voltage		V_{GS}	± 10	V
Drain Current	$T_A = 25^\circ\text{C}$	I_D	16	A
	$T_A = 100^\circ\text{C}$		10	
Pulsed Drain Current ^A		I_{DM}	64	A
Total Power Dissipation ^C	$T_A = 25^\circ\text{C}$	P_D	1	W
	$T_A = 100^\circ\text{C}$		0.4	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	29	36	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	3.6	4.5	$^\circ\text{C/W}$

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V	-	-	1	μA
		V _{DS} =20V, V _{GS} =0V, T _J =150°C	-	-	100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±10V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	0.4	0.7	1.0	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =4.5A	-	8.7	11	mΩ
		V _{GS} =2.5V, I _D =3.0A	-	12	15.5	
Diode Forward Voltage	V _{SD}	I _S =4.5A, V _{GS} =0V	-	0.9	1.2	V
Gate resistance	R _G	f=1MHz, Open drain	-	3.3	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	16	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1MHz	-	551	-	pF
Output Capacitance	C _{oss}		-	119	-	
Reverse Transfer Capacitance	C _{rss}		-	104	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =10V, I _D =4.5A	-	11	-	nC
Gate-Source Charge	Q _{gs}		-	1	-	
Gate-Drain Charge	Q _{gd}		-	2	-	
Reverse Recovery Charge	Q _{rr}	I _F =4.5A, di/dt=165A/us	-	4	-	nC
Reverse Recovery Time	t _{rr}		-	10	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =10V, I _D =4.5A R _{GEN} =2.2Ω	-	3.5	-	ns
Turn-on Rise Time	t _r		-	26	-	
Turn-off Delay Time	t _{D(off)}		-	19	-	
Turn-off fall Time	t _f		-	2.5	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. P_d is based on max. junction temperature, using junction-case thermal resistance.

C. The value of R_{θJA} is measured with the device mounted on the minimum recommend pad size, in the still air environment with T_A =25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

■ Typical Electrical and Thermal Characteristics Diagrams

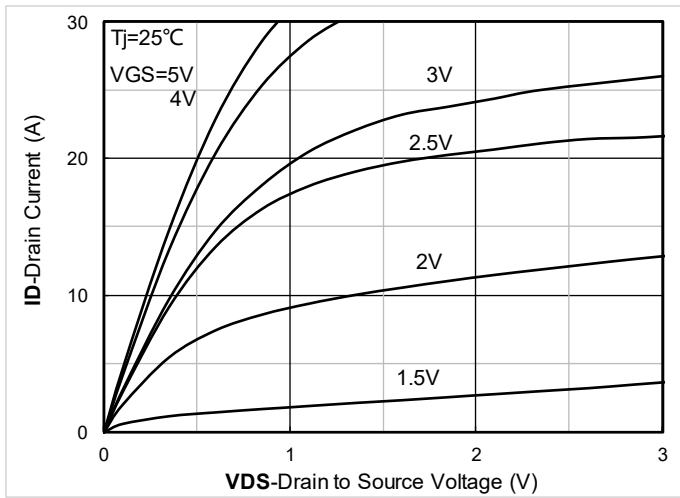


Figure 1. Output Characteristics

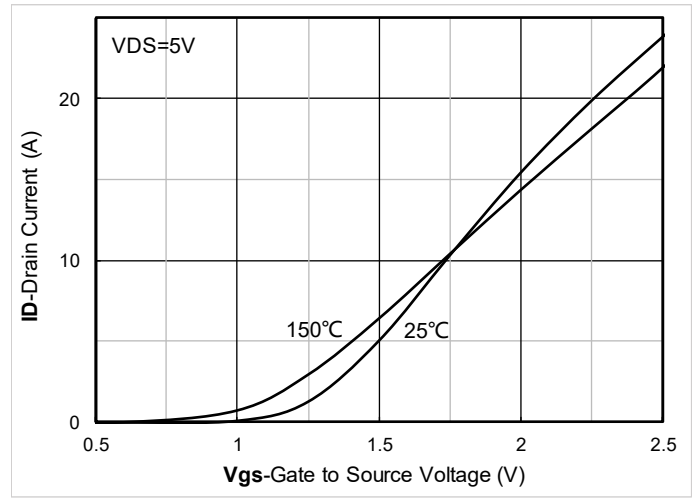


Figure 2. Transfer Characteristics

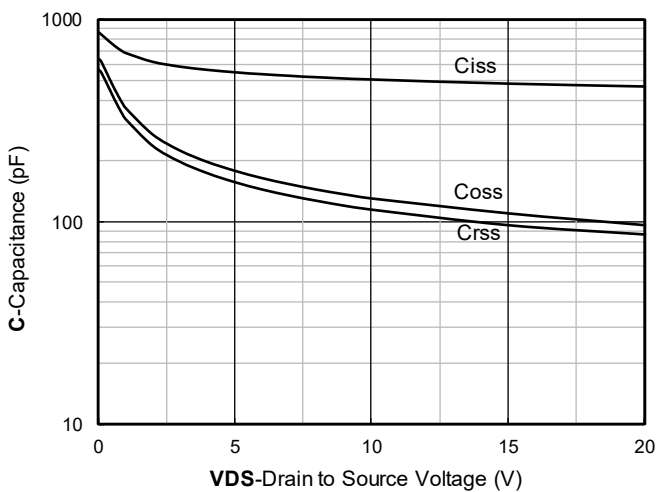


Figure 3. Capacitance Characteristics

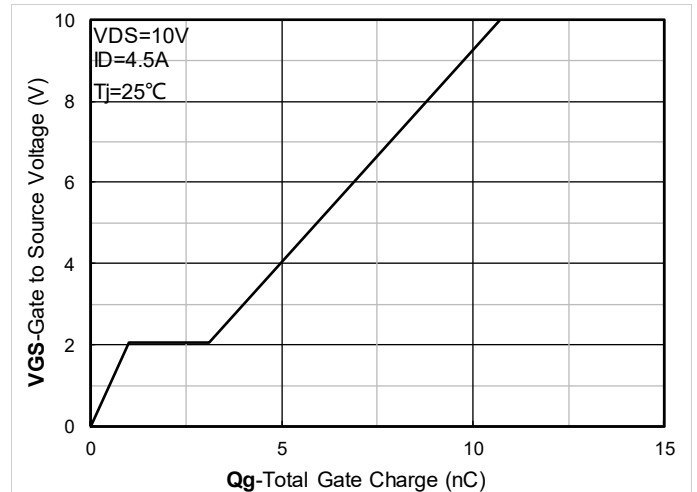


Figure 4. Gate Charge

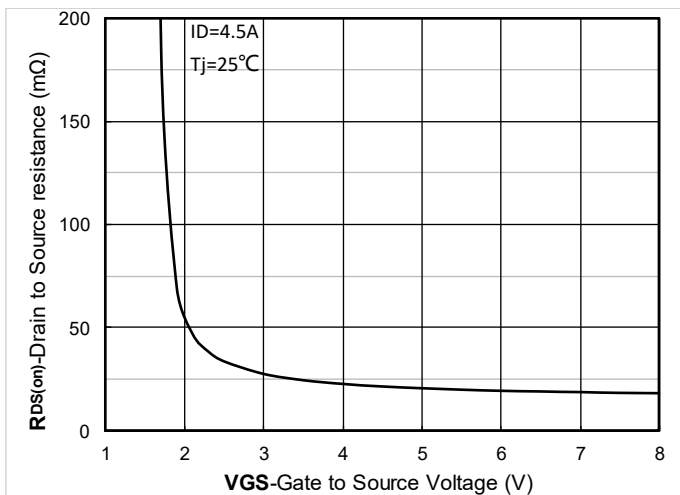


Figure 5. On-Resistance vs Gate to Source Voltage

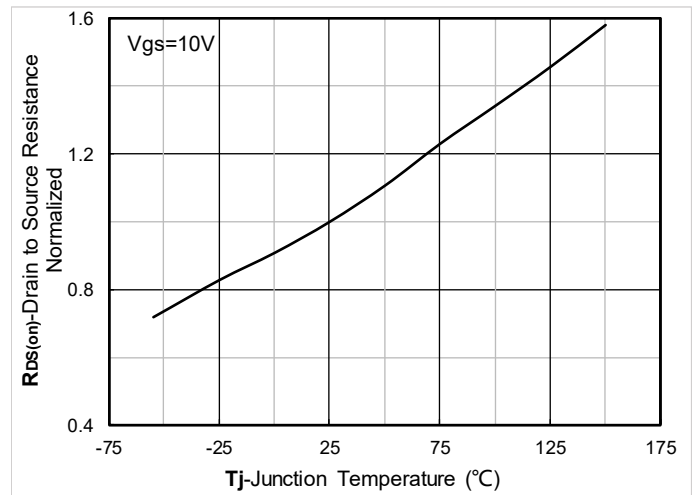


Figure 6. Normalized On-Resistance

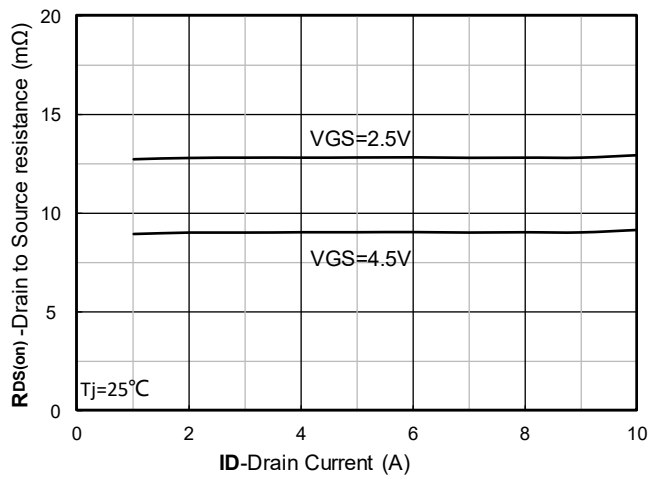


Figure 7. RDS(on) VS Drain Current

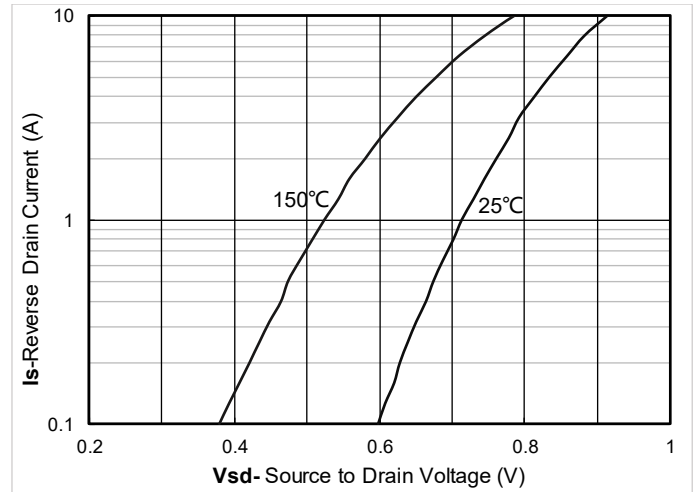


Figure 8. Forward characteristics of reverse diode

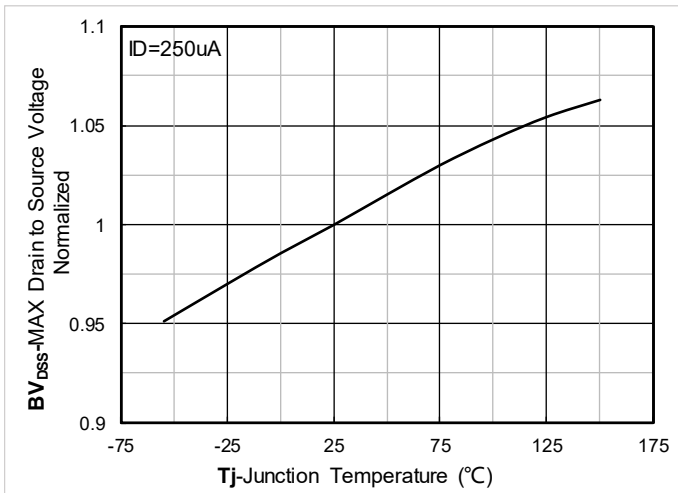


Figure 9. Normalized breakdown voltage

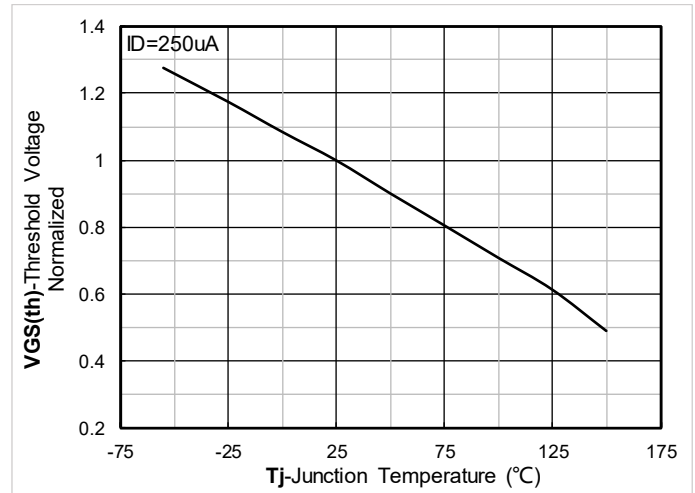


Figure 10. Normalized Threshold voltage

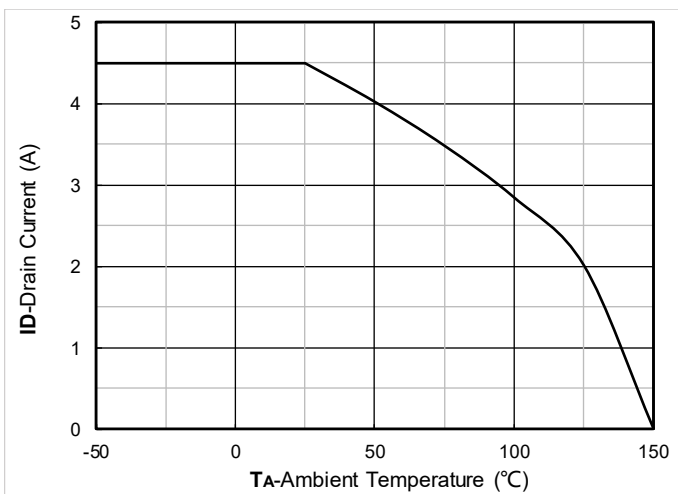


Figure 11. Current dissipation

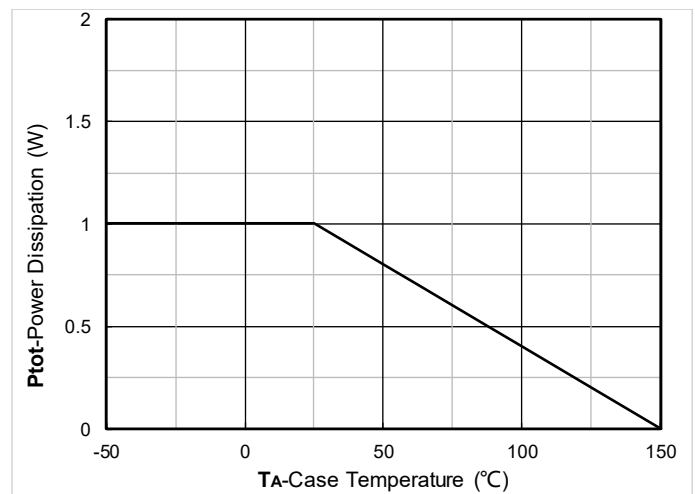


Figure 12. Power dissipation

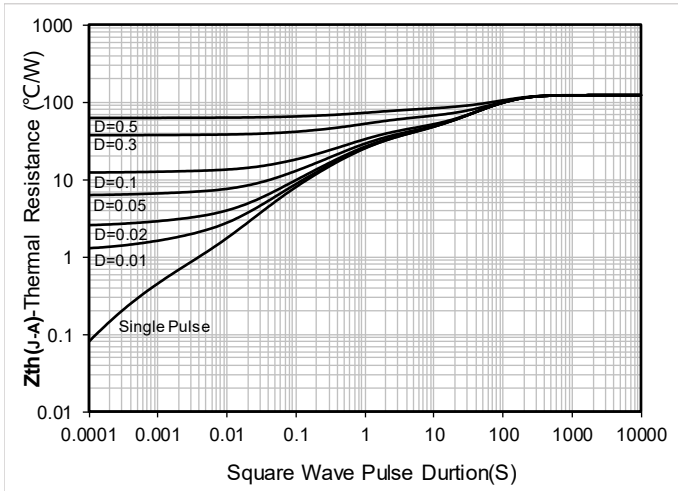


Figure 13. Maximum Transient Thermal Impedance

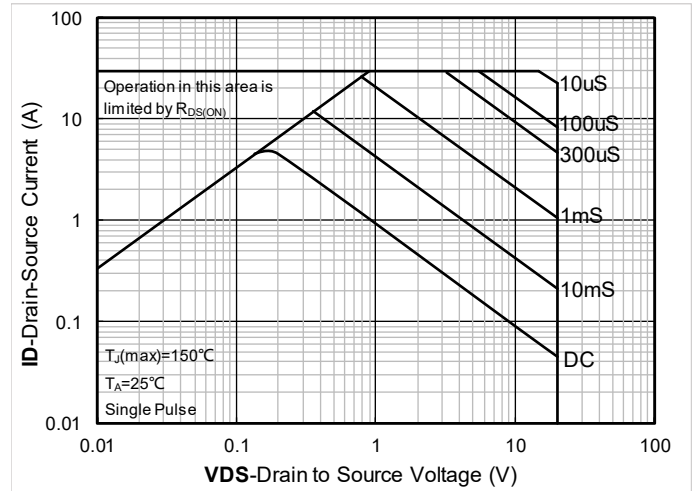


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

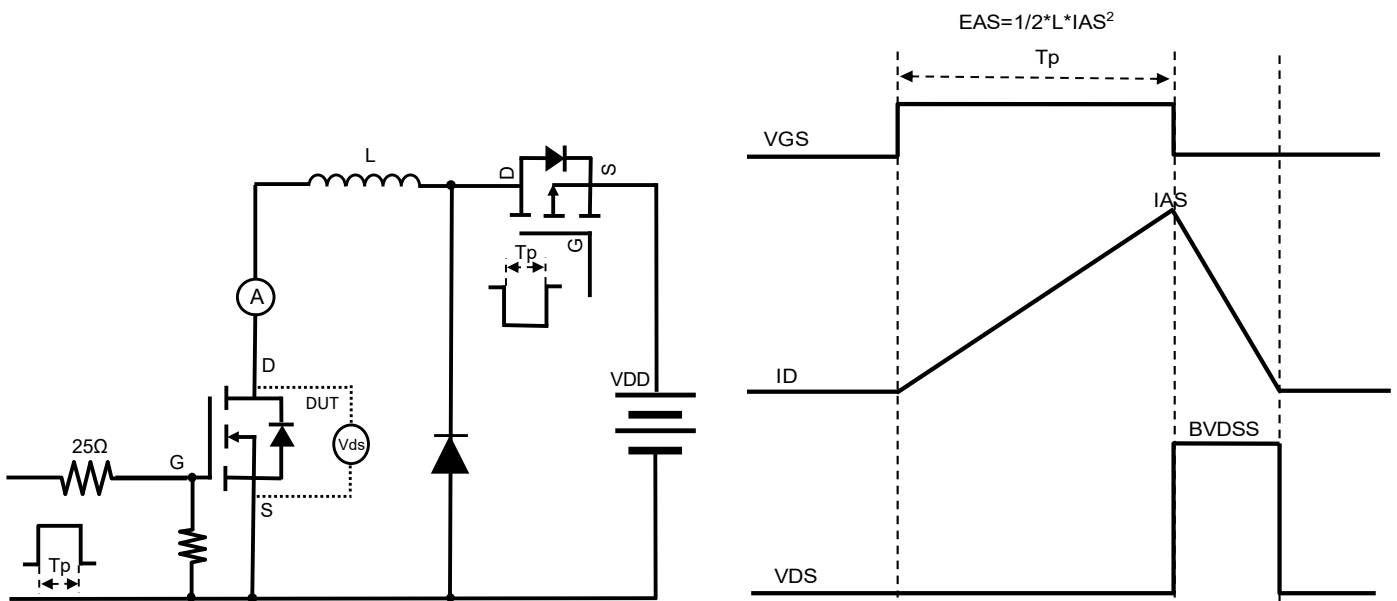


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

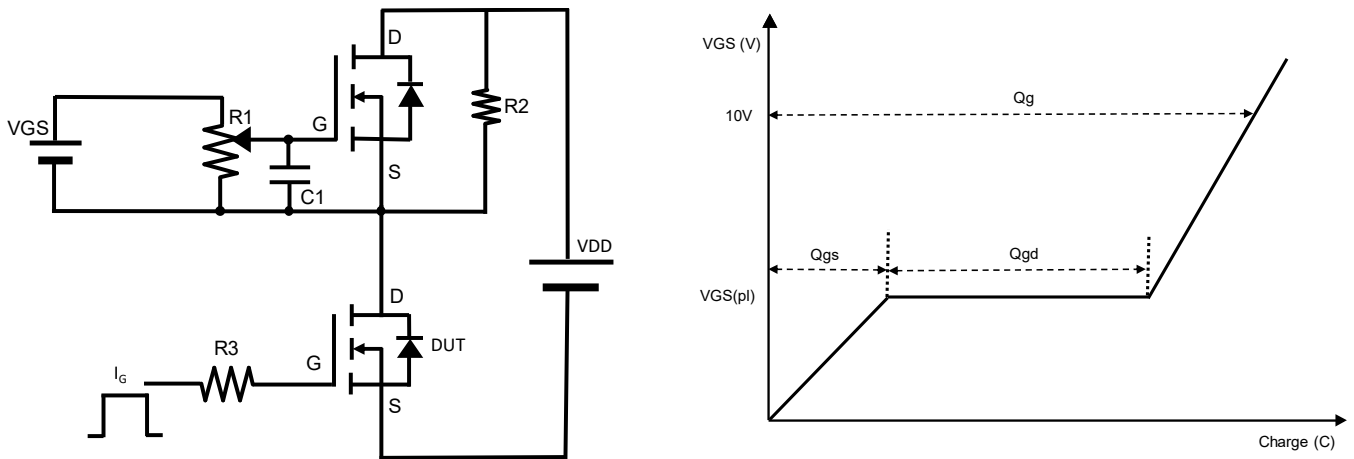


Figure B. Gate Charge Test Circuit & Waveform

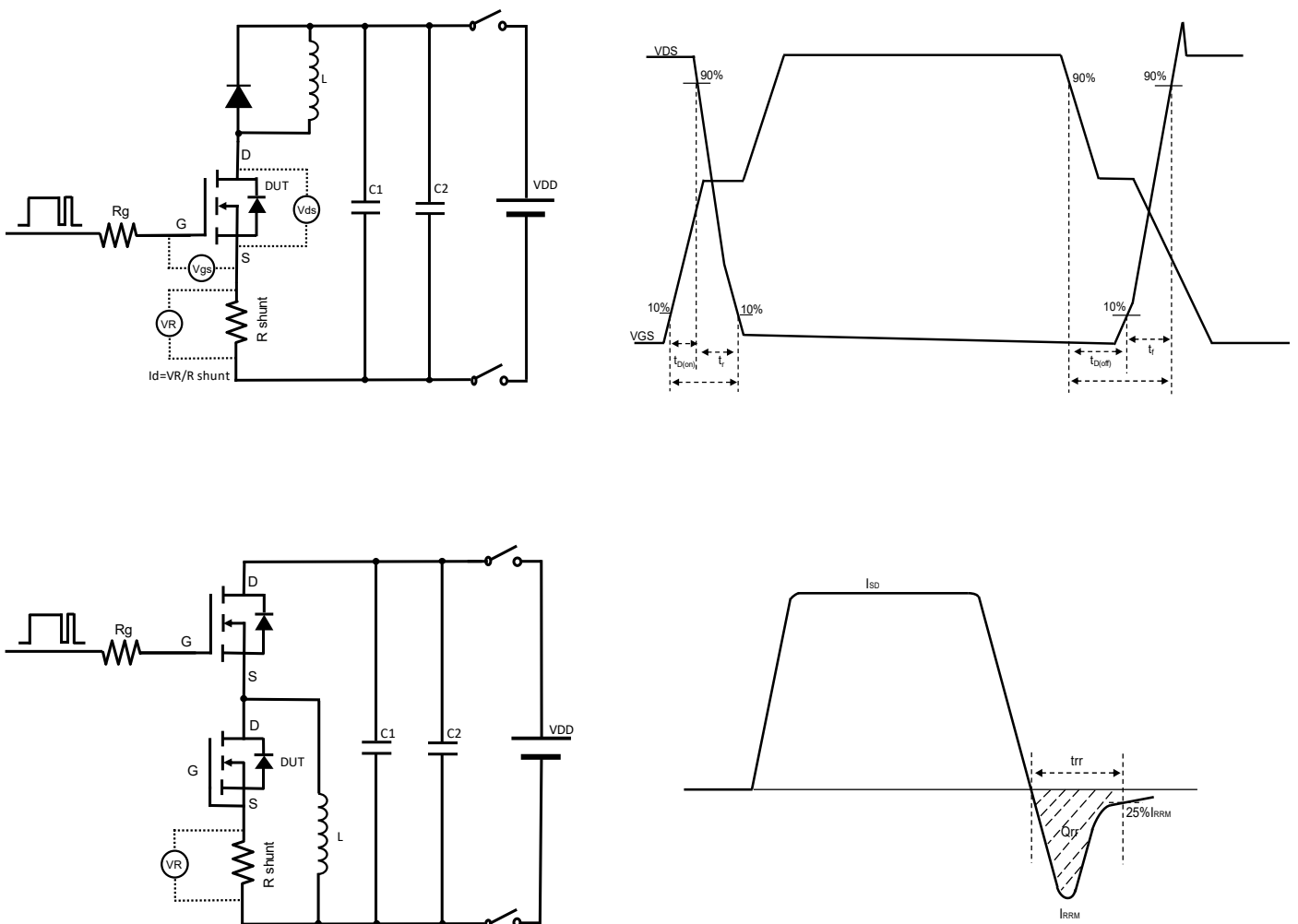
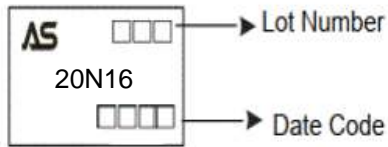
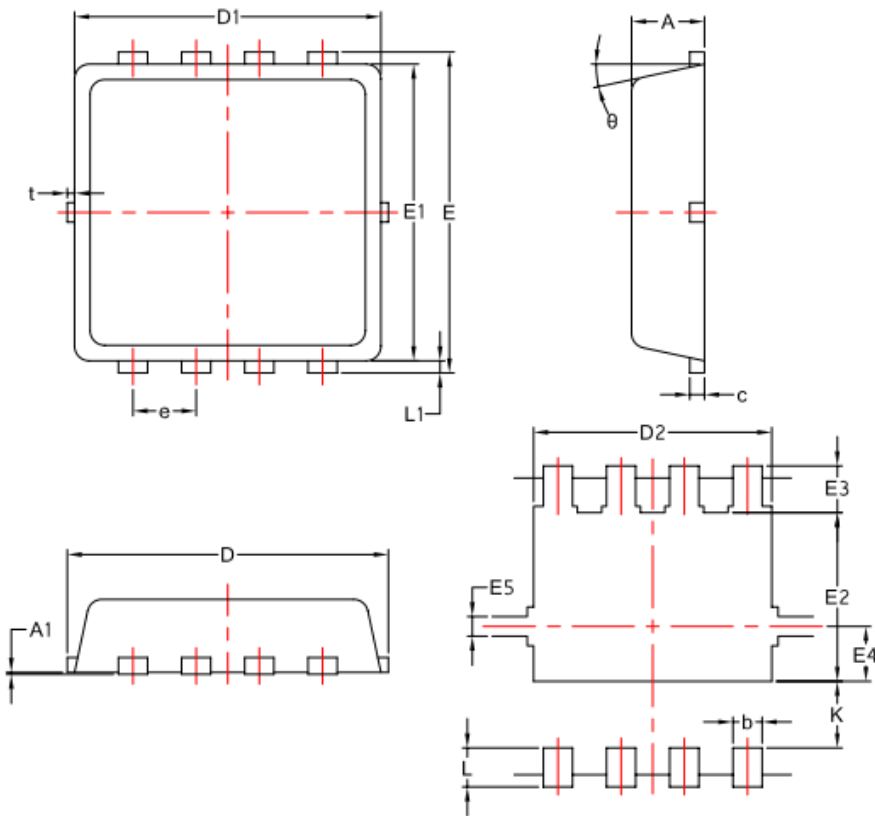


Figure D. Diode Recovery Test Circuit & Waveform

Ordering and Marking Information

Ordering Device No.	Marking	Package	Packing	Quantity
ASDM20N16E-R	20N16	PDFN3.3x3.3-8	Tape&Reel	5000/Reel

PACKAGE	MARKING
PDFN3.3x3.3-8	 <p>AS □□□□ → Lot Number 20N16 □□□□ → Date Code</p>



SYMBOL	COMMON		
	MM		
	MIN	NOM	MAX
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
△ D1	3.00	3.15	3.25
△ D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
△ E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
△ K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
△ t	0	0.075	0.13
△ θ	10°	12°	14°

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